

# isc N-Channel MOSFET Transistor

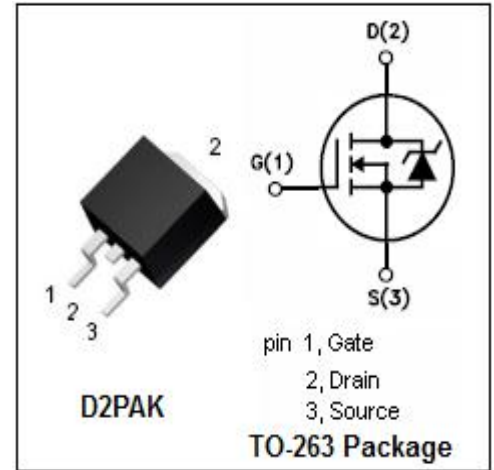
# IPB65R110CFD

### • FEATURES

- With TO-263(D2PAK) packaging
- Ultra-fast body diode
- High speed switching
- Very high commutation ruggedness
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operationz

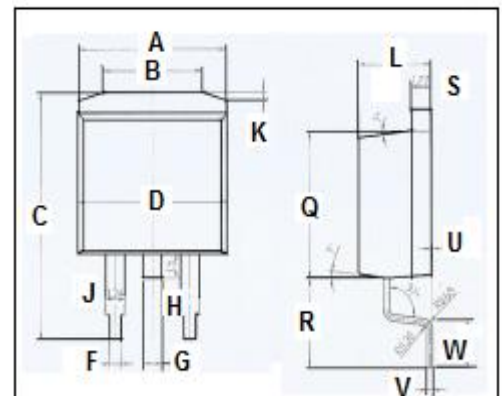
### • APPLICATIONS

- Switching applications



### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	650	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	31.2 19.7	A
$I_{DM}$	Drain Current-Single Pulsed	99.6	A
$P_D$	Total Dissipation	277.8	W
$T_j$	Operating Junction Temperature	-55~150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^{\circ}\text{C}$



DIM	mm	
	MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.45	$^{\circ}\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C}/\text{W}$

**isc N-Channel MOSFET Transistor****IPB65R110CFD****ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 1mA	650			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =±20V; I <sub>D</sub> =1.3mA	3.5		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =12.7A		99	110	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V@T <sub>C</sub> =25°C T <sub>C</sub> =125°C			1.5 400	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =19.1A, V <sub>GS</sub> = 0 V			0.9	V

**NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.